

# High Voltage Transistor

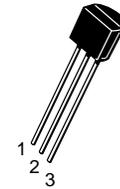
## NPN Silicon

# MPSA44

ON Semiconductor Preferred Device

### MAXIMUM RATINGS

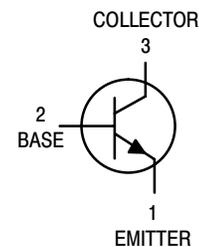
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	400	Vdc
Collector–Base Voltage	$V_{CBO}$	500	Vdc
Emitter–Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current — Continuous	$I_C$	300	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$



CASE 29-11, STYLE 1  
TO-92 (TO-226AA)

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	400	—	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = 100 \mu\text{Adc}, V_{BE} = 0$ )	$V_{(BR)CES}$	500	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu\text{Adc}, I_E = 0$ )	$V_{(BR)CBO}$	500	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 400 \text{ Vdc}, I_E = 0$ )	$I_{CBO}$	—	0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = 400 \text{ Vdc}, V_{BE} = 0$ )	$I_{CES}$	—	500	nAdc
Emitter Cutoff Current ( $V_{EB} = 4.0 \text{ Vdc}, I_C = 0$ )	$I_{EBO}$	—	0.1	$\mu\text{Adc}$

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MPSA44

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS<sup>(1)</sup></b>				
DC Current Gain <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	$h_{FE}$	40 50 45 40	— 200 — —	—
Collector–Emitter Saturation Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}$ , $I_B = 0.1 \text{ mAdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	$V_{CE(sat)}$	— — —	0.4 0.5 0.75	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ )	$V_{BE(sat)}$	—	0.75	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Output Capacitance ( $V_{CB} = 20 \text{ Vdc}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{obo}$	—	7.0	pF
Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}$ , $I_C = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{ibo}$	—	130	pF
Small–Signal Current Gain ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 20 \text{ MHz}$ )	$h_{fe}$	1.0	—	—

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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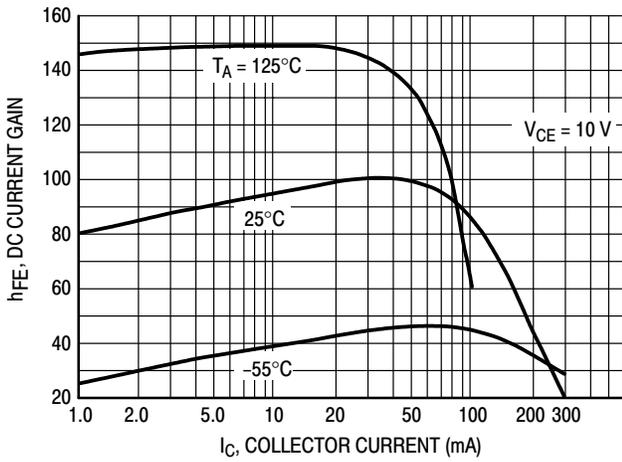


Figure 1. DC Current Gain

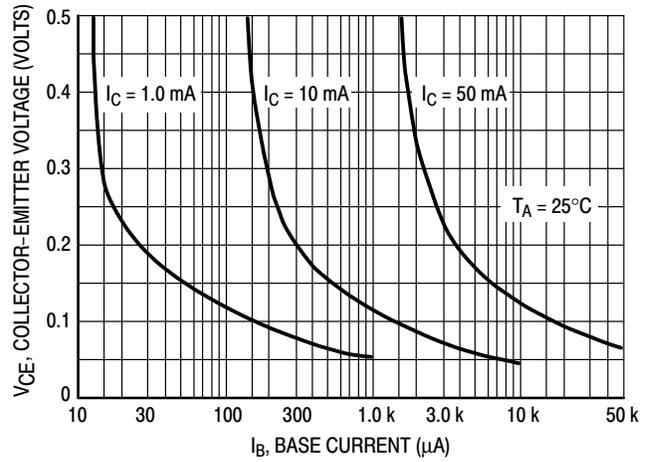


Figure 2. Collector Saturation Region

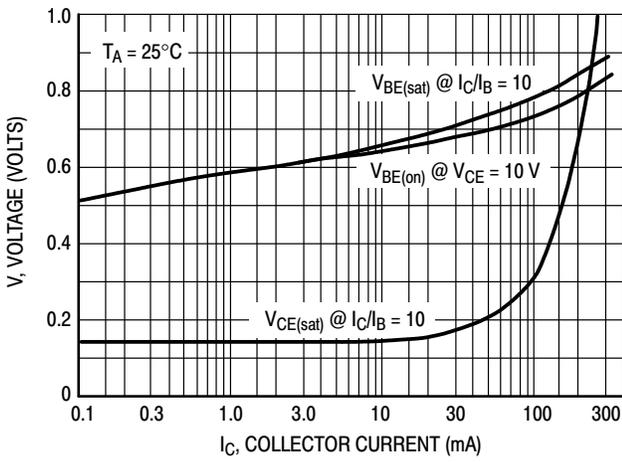


Figure 3. "On" Voltages

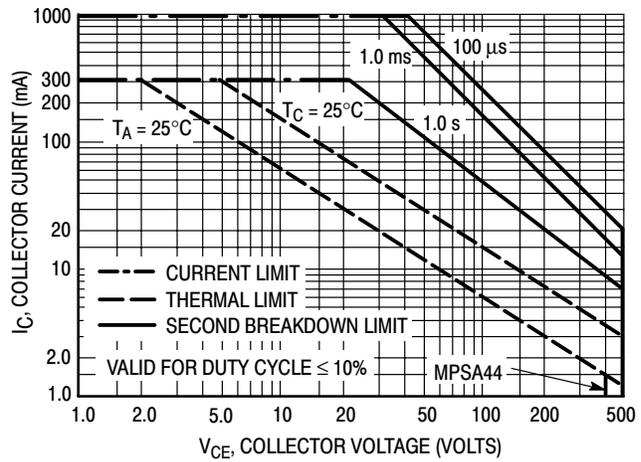


Figure 4. Active Region — Safe Operating Area

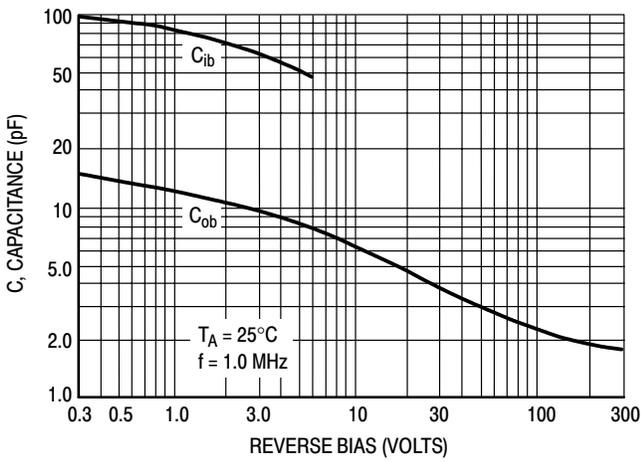


Figure 5. Capacitance

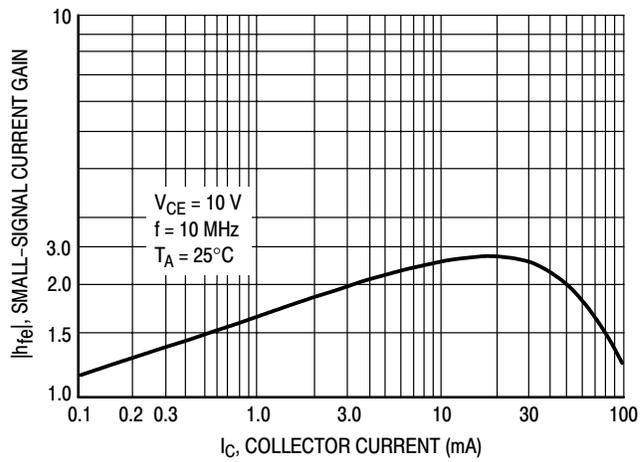


Figure 6. High Frequency Current Gain

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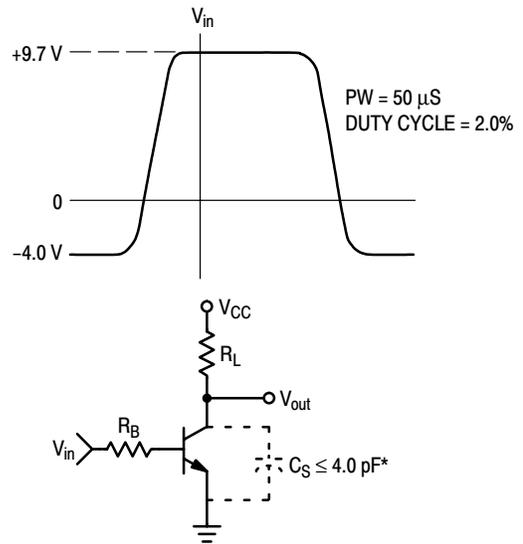
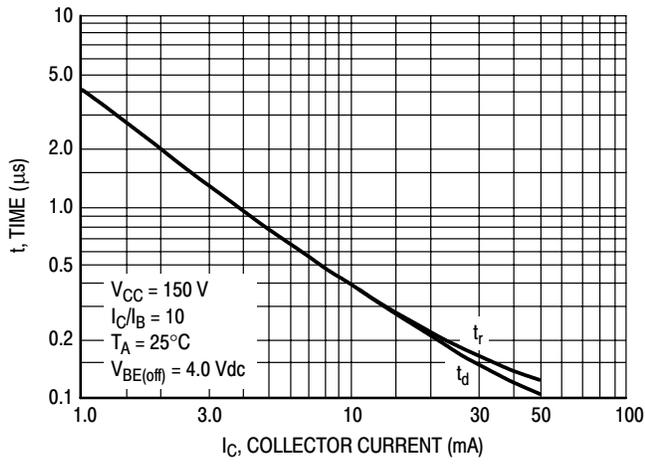


Figure 7. Turn-On Switching Times and Test Circuit

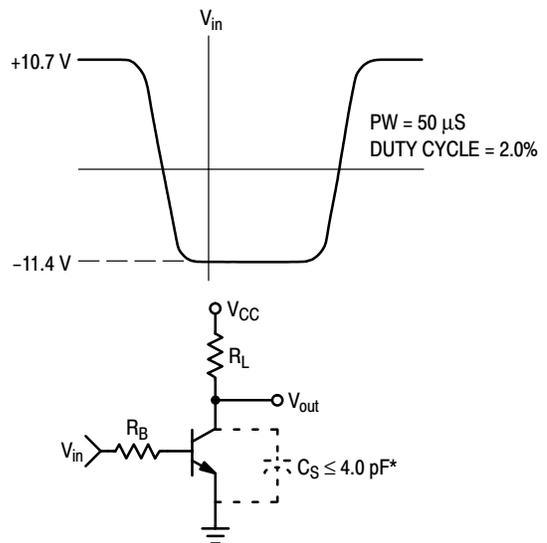
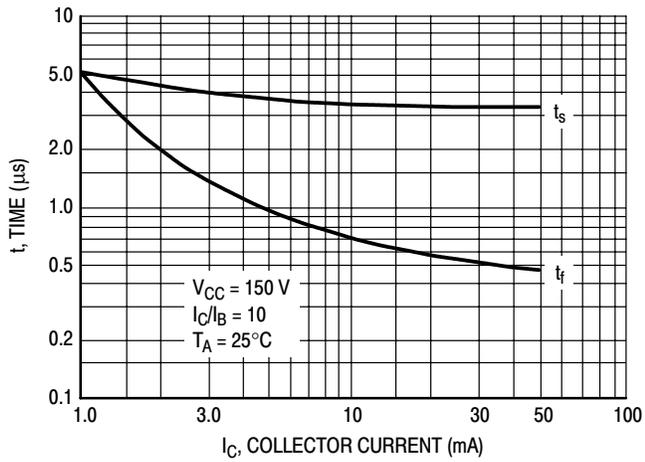


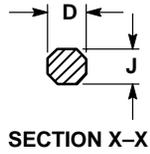
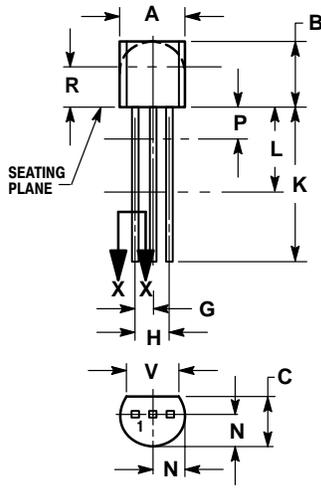
Figure 8. Turn-Off Switching Times and Test Circuit

\*Total Shunt Capacitance of Test Jig and Connectors.

# MPSA44

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

**Notes**

**Notes**

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